

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	229	sakaguchi near kiyofumi.in.	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 19:47	
2	BRS	L2	0	438/305.\$ccls.	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 19:47	
3	BRS	L3	2065	438/305.ccls.	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 19:48	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	0	3 and (separation near layer) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/12 19:48	
5	BRS	L5	41	3 and (separation) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/12 19:49	
6	BRS	L6	24468	(separation) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/12 19:49	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	1323	(separation near layer) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 19:50	
8	BRS	L8	133	(separation near layer) near25 (second near substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 19:50	
9	BRS	L9	7	(separation near layer) near25 (second near substrate) near25 (implant\$3)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 19:53	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	959	(second near substrate) near25 (implant\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 19:54	
11	BRS	L11	210	(second near substrate) near25 (first near substrate) near25 (implant\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 20:15	
12	BRS	L12	959	(second near substrate) near25 (implant\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 20:16	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	50	(second near substrate) near25 (implant\$3) near35 (semiconductor near layer)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/1 2 20:16	

	U	1	Document ID	Title	Current OR	Pages
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040048454 A1	Substrate and manufacturing method therefor	438/486	27
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030170990 A1	PROCESS FOR MANUFACTURING A SEMICONDUCTOR SUBSTRATE AS WELL AS A SEMICONDUCTOR THIN FILM, AND MULTILAYER STRUCTURE	438/690	42
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20030038383 A1	Semiconductor substrate and process for its production	257/797	32
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20010038153 A1	Semiconductor substrate and process for its production	257/797	32
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6700631 B1	Method of separating thin-film device, method of transferring thin-film device, thin-film device, active matrix substrate, and liquid crystal display device	349/45	35
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6613678 B1	Process for manufacturing a semiconductor substrate as well as a semiconductor thin film, and multilayer structure	438/695	42
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	EP 961312 A2	SOI Substrate formed by bonding		47